

## 1. Global joint venture starts operations as WeEn Semiconductors

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Product data sheet

## 1. Product profile

#### 1.1 General description

Ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

#### 1.2 Features and benefits

- Fast switching
- High thermal cycling performance
- Low forward volt drop

- Low thermal resistance
- Soft recovery minimizes power-consuming oscillations

### 1.3 Applications

Discontinuous Current Mode (DCM)
 Power Factor Correction (PFC)

 Output rectifiers in high-frequency switched-mode power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	-	400	V
I <sub>F(AV)</sub>	average forward current	square-wave pulse; $\bar{\delta} = 0.5$ ; $T_{mb} \le 123$ °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	9	A
Static cha	racteristics					
$V_{F}$	forward voltage	$I_F = 8 \text{ A}; T_j = 150 \text{ °C}; \text{ see } \frac{\text{Figure 4}}{\text{Minimum 1}}$	-	0.9	1.03	V
Dynamic o	haracteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/s}$ ; $T_j = 25 \text{ °C}$ ; see Figure 7; see Figure 5	-	50	60	ns



Ultrafast power diode

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	Α	anode	mb	K <del>     </del> A 001aaa020
mb	mb	mounting base; cathode	ζ O 1	
			Ü	
			1 2 SOD59 (TO-220AC)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYV29-400	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		,			
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	400	V
$V_{RWM}$	crest working reverse voltage		-	400	V
$V_R$	reverse voltage	DC	-	400	V
I <sub>F(AV)</sub>	average forward current	square-wave pulse; $\delta = 0.5$ ; $T_{mb} \le 123$ °C; see Figure 1; see Figure 2	-	9	Α
I <sub>FRM</sub>	repetitive peak forward current	square-wave pulse; $\delta = 0.5$ ; $t_p = 25 \mu s$ ; $T_{mb} \le 123  ^{\circ}C$	-	18	Α
I <sub>FSM</sub>	non-repetitive peak forward	sine-wave pulse; $t_p = 10 \text{ ms}$ ; $T_{j(init)} = 25 \text{ °C}$	-	100	Α
	current	sine-wave pulse; $t_p = 8.3 \text{ ms}$ ; $T_{j(init)} = 25 \text{ °C}$	-	110	Α
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

NXP Semiconductors BYV29-400

Ultrafast power diode

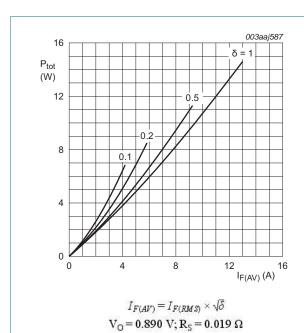


Fig 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

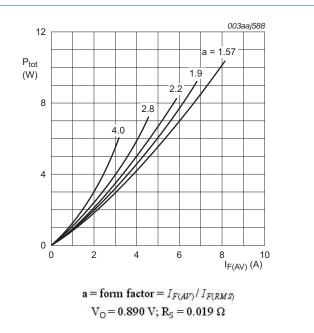


Fig 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

Ultrafast power diode

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 3	-	-	2.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

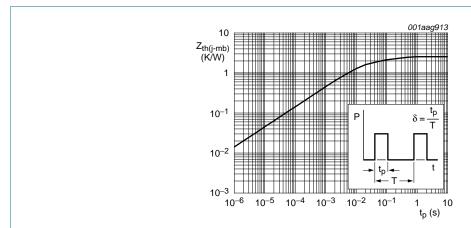
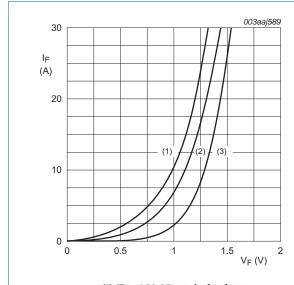


Fig 3. Transient thermal impedance from junction to mounting base as a function of pulse width

### 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>F</sub>	forward voltage	$I_F = 8 \text{ A}; T_j = 150 \text{ °C}; \text{ see } \frac{\text{Figure 4}}{}$	-	0.9	1.03	V
		$I_F = 8 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 4}}{}$	-	1.05	1.25	V
		$I_F = 20 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 4}}{}$	-	1.2	1.4	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 400 V; T <sub>j</sub> = 25 °C	-	2	50	μΑ
		V <sub>R</sub> = 400 V; T <sub>j</sub> = 100 °C	-	0.1	0.35	mΑ
Dynamic (	characteristics					
Q <sub>r</sub>	recovered charge	$I_F = 2 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 20 \text{ A/s}$ ; $T_j = 25 \text{ °C}$ ; see Figure 5; see Figure 6	-	40	60	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/s}$ ; $T_j = 25 \text{ °C}$ ; see Figure 7; see Figure 5	-	50	60	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 10 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 50 \text{ A/s}$ ; $T_j = 100 \text{ °C}$ ; see Figure 8; see Figure 5	-	4	5.5	Α
$V_{FRM}$	forward recovery voltage	$I_F = 10 \text{ A}$ ; $dI_F/dt = 10 \text{ A/s}$ ; $T_j = 25 \text{ °C}$ ; see Figure 9	-	2.5	-	V



(1)  $T_j = 150$  °C; typical values;

(2)  $T_j = 150$  °C; maximum values;

(3)  $T_j = 25$  °C; maximum values;  $V_O = 0.890$  V;  $R_S = 0.019$   $\Omega$ 

Fig 4. Forward current as a function of forward voltage

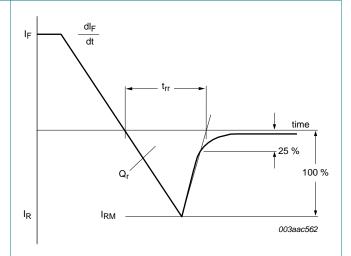
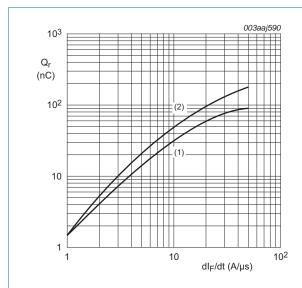


Fig 5. Reverse recovery definitions; ramp recovery



(1) 
$$I_F = 2 A$$
;  $T_j = 25 °C$ ;

(2) 
$$I_F = 10 \text{ A}$$
;  $T_j = 25 \text{ }^{\circ}\text{C}$ 

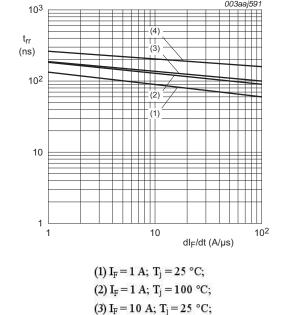
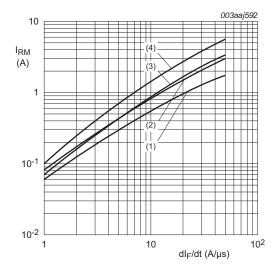


Fig 7. Reverse recovery time as a function of rate of change of forward current; maximum values

(4)  $I_F = 10 \text{ A}; T_i = 100 \text{ }^{\circ}\text{C}$ 





(1) 
$$I_F = 1 A$$
;  $T_i = 25 \, ^{\circ}\text{C}$ ;

(2) 
$$I_F = 1 A$$
;  $T_i = 100 \, ^{\circ}C$ ;

(3) 
$$I_F = 10 A; T_j = 25 °C;$$

(4) 
$$I_F = 10 A$$
;  $T_j = 100 °C$ 

Fig 8. Peak reverse recovery current as a function of rate of change of forward current; maximum values

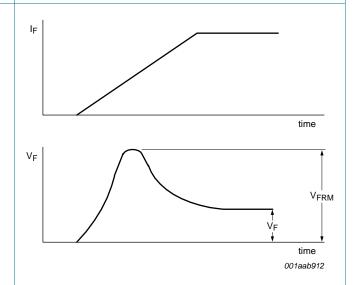


Fig 9. Forward recovery definitions

## 7. Package outline

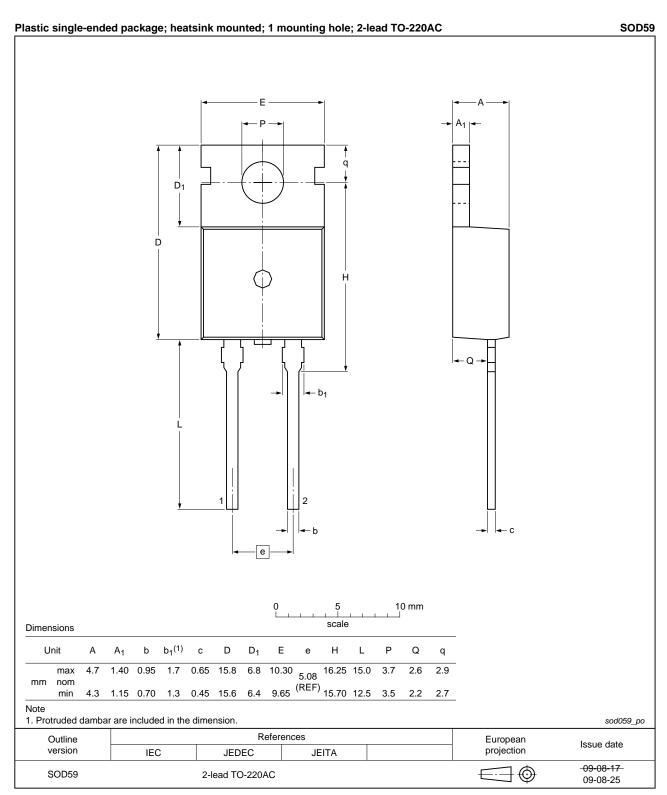


Fig 10. Package outline SOD59 (TO-220AC)

**BYV29-400** 

Ultrafast power diode

# 8. Revision history

## Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV29-400 v.3	20120529	Product data sheet	-	BYV29_SERIES v.2
Modifications:	<ul><li>Type number BY</li><li>Various changes</li></ul>	V29-400 separated from on to content.	lata sheet BYV29_SER	RIES v.2.
BYV29_SERIES v.2	19980901	Product specification	-	BYV29_SERIES v.1

## 9. Legal information

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Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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BYV29-400

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#### Ultrafast power diode

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## Ultrafast power diode

## 11. Contents

1	Product profile	.1
1.1	General description	.1
1.2	Features and benefits	.1
1.3	Applications	.1
1.4	Quick reference data	.1
2	Pinning information	.2
3	Ordering information	.2
4	Limiting values	.2
5	Thermal characteristics	.4
6	Characteristics	.5
7	Package outline	.7
8	Revision history	.8
9	Legal information	.9
9.1	Data sheet status	.9
9.2	Definitions	.9
9.3	Disclaimers	.9
9.4	Trademarks	10
10	Contact information	10

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